Featured Products











IGBTs)

Low V_{CE(sat)} contributes to lower power consumption

Bipolar Transistors Ideal for Gate Drive Circuits (for SiC/IGBTs/Super Junction MOSFETs)

2SARxxx(PNP)/2SCRxxx(NPN)

Low saturation voltage $V_{CE(sat)}$ series

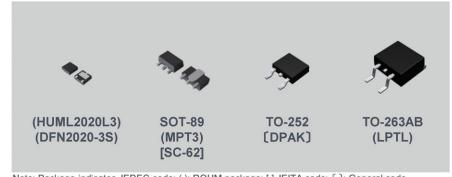
Large collector current

Broad package lineup

DFN2020-3S, SOT-89, TO-252, TO-263AB

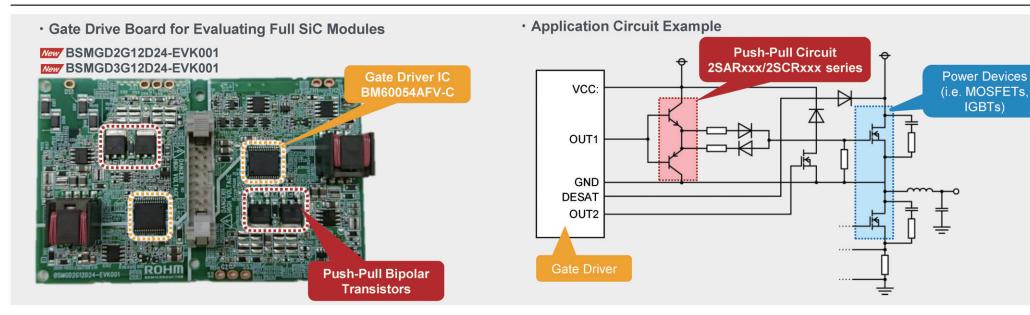
Automotive-grade(AEC-Q101 qualified)*

*SOT-89, TO-252, TO-263AB



Note: Package indicates JEDEC code; (): ROHM package; [] JEITA code; (): General code

Optimized for Gate Drive Circuits



■ Bipolar Transistors for Gate Drive Circuits (ROHM offers a broad lineup of bipolar transistors in addition to the models below)

	PD	Polarity	Part No.		V _{CEO}		I _{CP} *⁴		V _{CE(sat)}
Package	(W)		Consumer	Automotive (AEC-Q101)	(V)	I _C (A)	(A)	h _{FE}	Ty p(mV) I _C =0.5A/I _B =0.05A
(HUML2020L3) [DFN2020-3S] 2.0×2.0×0.6mm		PNP	New 2SAR563F3	_	- 50	- 6	-12	180 to 450	- 50
	2.1* ¹		New 2SAR564F3	_	- 80	- 4	- 8	120 to 390	- 60
	2.1	NPN	New 2SCR563F3	_	50	6	12	180 to 450	35
			New 2SCR564F3	_	80	4	8	120 to 390	40
SOT-89 (MPT3) [SC-62] 4.5×4.0×1.5mm		PNP	2SAR533P5	2SAR533P HZG	- 50	- 3	- 6	180 to 450	-120
	2* ²		2SAR544P5	2SAR544P HZG	- 80	-2.5	- 5	120 to 390	- 90
	2	NPN	2SCR533P5	2SCR533P HZG	50	3	6	180 to 450	60
			2SCR544P5	2SCR544P HZG	80	2.5	5	120 to 390	50
TO-252 [DPAK] 6.6×10.0×2.2mm		PNP	2SAR583D3	☆2SAR583D3 FRA	- 50	- 7	-14	180 to 450	- 40
	10* ³		2SAR586D3	2SAR586D3 FRA	- 80	- 5	-10	120 to 390	- 40
	10	NPN	2SCR583D3	☆2SCR583D3 FRA	50	7	14	180 to 450	30
			2SCR586D3	2SCR586D3 FRA	80	5	10	120 to 390	30
TO-263AB (LPTL) 10.1×15.1×4.5mm	40*3	PNP	2SAR586J	2SAR586J FRG	- 80	- 5	-10	120 to 390	- 40
	40	NPN	2SCR586J	2SCR586J FRG	80	5	10	120 to 390	30

Note: Package indicates JEDEC code; (): ROHM package; [] JEITA code; (): General code

☆: Under Development

Applications Examples

- xEVs
- Charging stands
- · Data centers, servers, UPS
- · Solar power panels
- · FA, drivers, power supplies ...and more

Supports a broad range of applications



Related Pages

SiC Support Page https://www.rohm.com/power-device-support



For information on other products, please visit ROHM's website.



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The content specified in this document is correct as of August 1st, 2020.

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^{*1} Pw=10ms when mounted on an FR4 board (25.4x25.4x1.6mm, 645mm2 Cu pad); *2 When mounted on a 40x40x0.7mm ceramic board; *3 Tc=25C; *4 Pw=10ms, single pulse